

# Thyristor \ Diode Module

$$V_{RRM} = 2x 1800 V$$

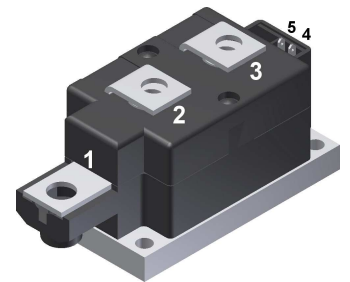
$$I_{TAV} = 220 A$$

$$V_T = 0,97 V$$

Phase leg

Part number

**MCD225-18io1**



Backside: isolated

 E72873



## Features / Advantages:

- International standard package
- Direct copper bonded Al<sub>2</sub>O<sub>3</sub>-ceramic with copper base plate
- Planar passivated chip
- Keyed gate/cathode twin pins

## Applications:

- Motor control, softstarter
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Solid state switches

## Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

## Disclaimer Notice

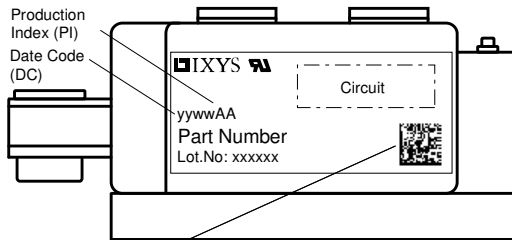
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Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1900	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1800	V	
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1800 V$	$T_{VJ} = 25^{\circ}C$		1	mA	
		$V_{R/D} = 1800 V$	$T_{VJ} = 125^{\circ}C$		40	mA	
$V_T$	forward voltage drop	$I_T = 200 A$	$T_{VJ} = 25^{\circ}C$		1,04	V	
		$I_T = 400 A$			1,18	V	
		$I_T = 200 A$	$T_{VJ} = 125^{\circ}C$		0,97	V	
		$I_T = 400 A$			1,14	V	
$I_{TAV}$	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 140^{\circ}C$		220	A	
$I_{T(RMS)}$	RMS forward current	180° sine			400	A	
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}C$		0,79	V	
$r_T$	slope resistance				0,83	mΩ	
$R_{thJC}$	thermal resistance junction to case				0,157	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0,04		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		730	W	
$I_{TSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		8,00	kA	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		8,64	kA	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		6,80	kA	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		7,35	kA	
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		320,0	kA <sup>2</sup> s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		310,5	kA <sup>2</sup> s	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		231,2	kA <sup>2</sup> s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		224,4	kA <sup>2</sup> s	
$C_J$	junction capacitance	$V_R = 400V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		366	pF	
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 140^{\circ}C$		120	W	
		$t_p = 500 \mu s$			60	W	
$P_{GAV}$	average gate power dissipation				20	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}C; f = 50 \text{ Hz}$ repetitive, $I_T = 660 A$			100	A/μs	
		$t_p = 200 \mu s; di_G/dt = 1 A/\mu s;$ $I_G = 1 A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 220 A$			500	A/μs	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$	$T_{VJ} = 140^{\circ}C$		1000	V/μs	
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		2	V	
			$T_{VJ} = -40^{\circ}C$		3	V	
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		150	mA	
			$T_{VJ} = -40^{\circ}C$		220	mA	
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$		0,25	V	
$I_{GD}$	gate non-trigger current				10	mA	
$I_L$	latching current	$t_p = 30 \mu s$	$T_{VJ} = 25^{\circ}C$		200	mA	
		$I_G = 0,45 A; di_G/dt = 0,45 A/\mu s$					
$I_H$	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		150	mA	
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs	
		$I_G = 1 A; di_G/dt = 1 A/\mu s$					
$t_q$	turn-off time	$V_R = 100 V; I_T = 220 A; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s; dv/dt = 50 V/\mu s; t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		200	μs	



Package Y1			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			600	A
$T_{VJ}$	virtual junction temperature		-40		140	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				680		g
$M_D$	mounting torque		4,5		7	Nm
$M_T$	terminal torque		11		13	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	16,0			mm
$d_{Spb/Apb}$		terminal to backside	16,0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	4800			V
		t = 1 minute	4000			V



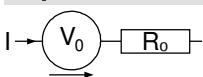
Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD225-18io1	MCD225-18io1	Box	3	473596

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 140^{\circ}C$

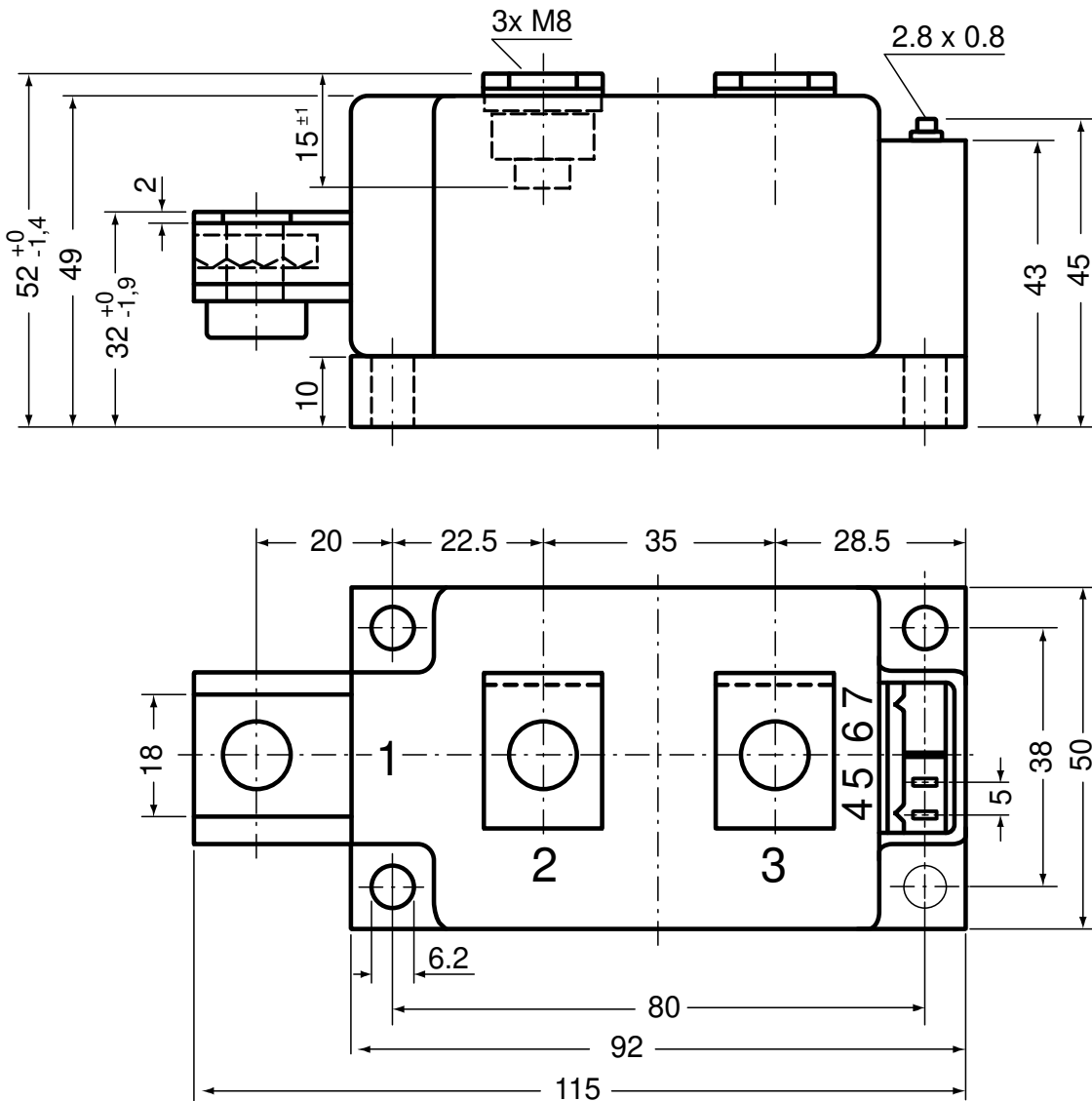


**Thyristor**

$V_{0\ max}$	threshold voltage	0,79	V
$R_{0\ max}$	slope resistance *	0,64	mΩ

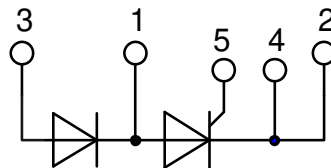


**Outlines Y1**



**Optional accessories for modules**

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red  
Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751





**Thyristor**

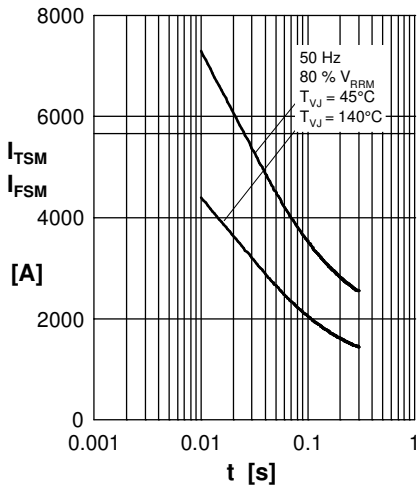


Fig. 1 Surge overload current  
 $I_{TSM/FSM}$ : Crest value,  $t$ : duration

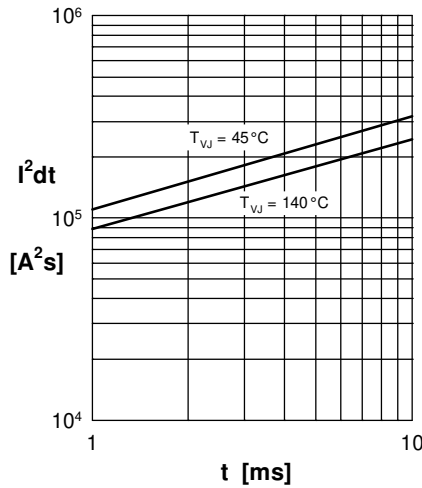


Fig. 2  $I^2dt$  versus time

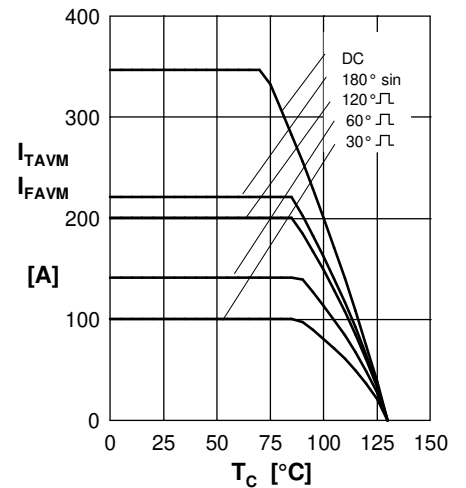


Fig. 3 Max. forward current at case temperature

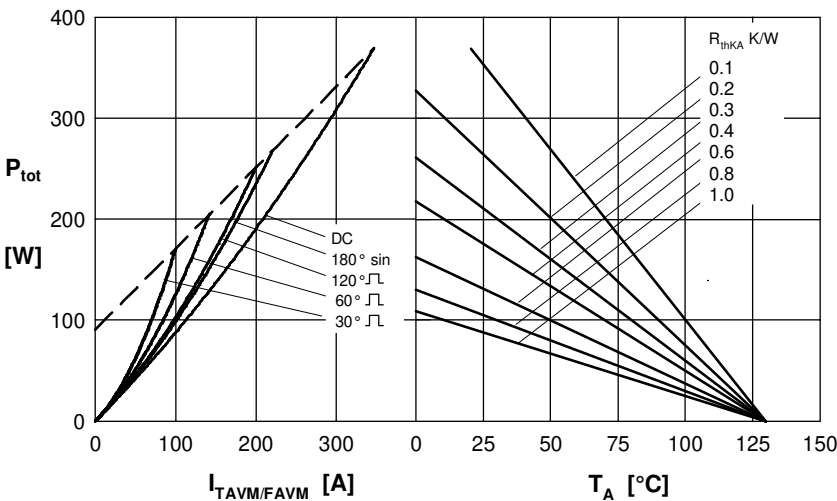


Fig. 4 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

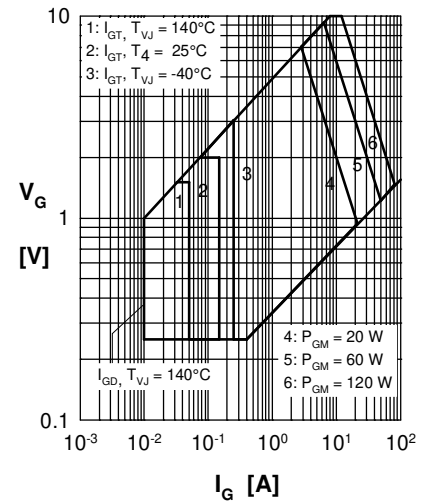


Fig. 5 Gate voltage and current

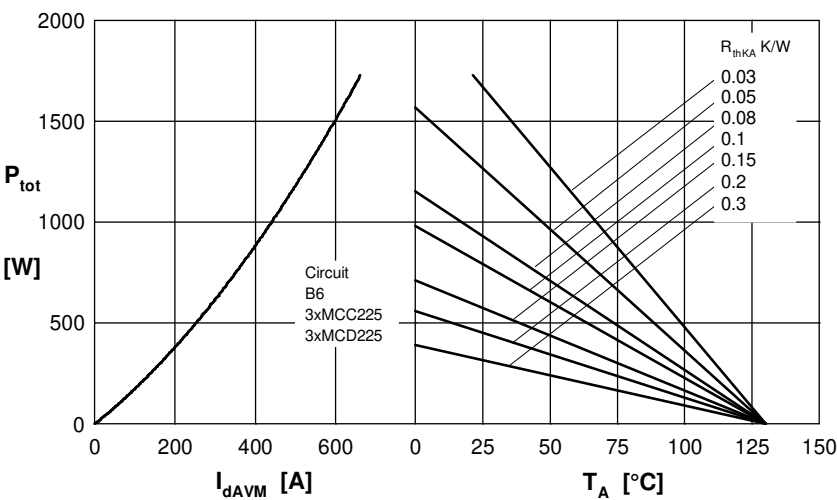


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

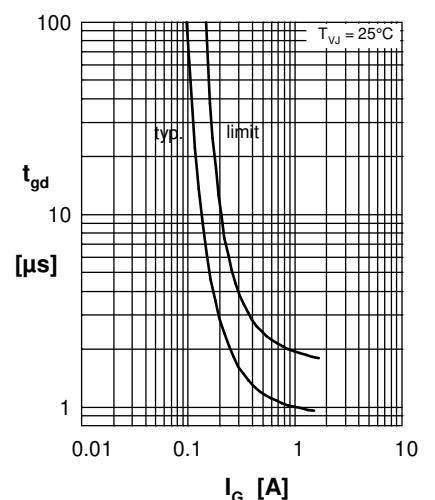


Fig. 7 Gate trigger characteristics

**Rectifier**

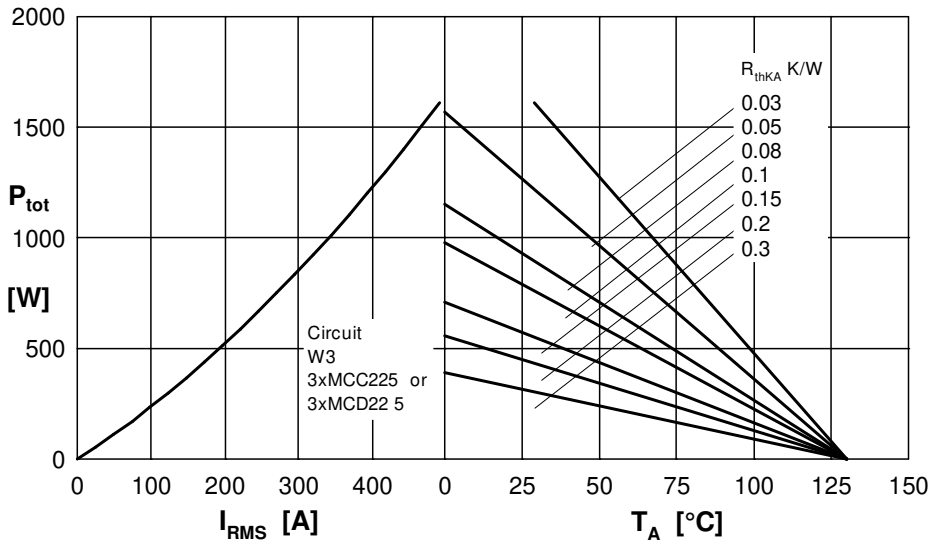


Fig. 8 Three phase AC-controller: Power dissipation versus  $R_{MS}$  output current and ambient temperature

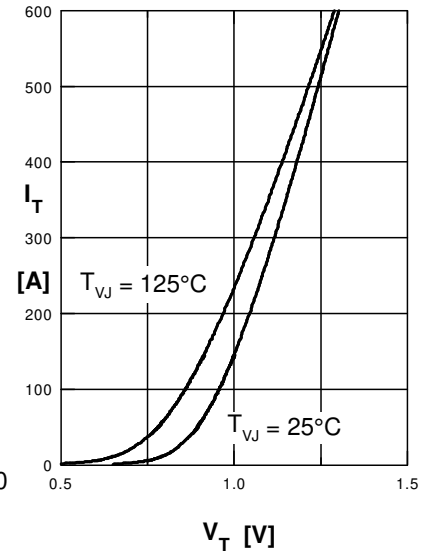


Fig. 9 Forward characteristics

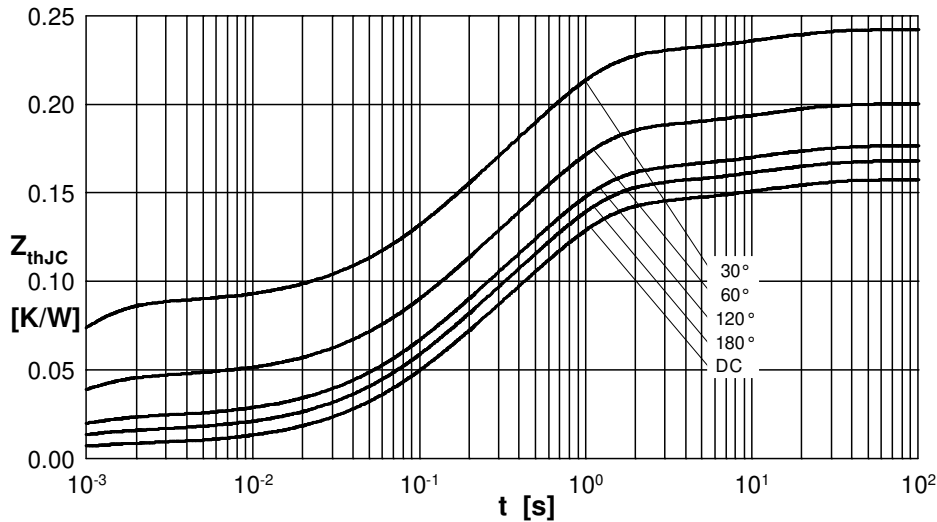


Fig. 10 Transient thermal impedance junction to case (per thyristor/diode)

$R_{thJC}$  for various conduct. angles d:

d	$R_{thJC}$ (K/W)
DC	0.157
180°	0.168
120°	0.177
60°	0.200
30°	0.243

Constants for  $Z_{thJC}$  calculation:

i	$R_{th}$ (K/W)	t (s)
1	0.0076	0.00054
2	0.0406	0.09800
3	0.0944	0.54000
4	0.0147	12.0000

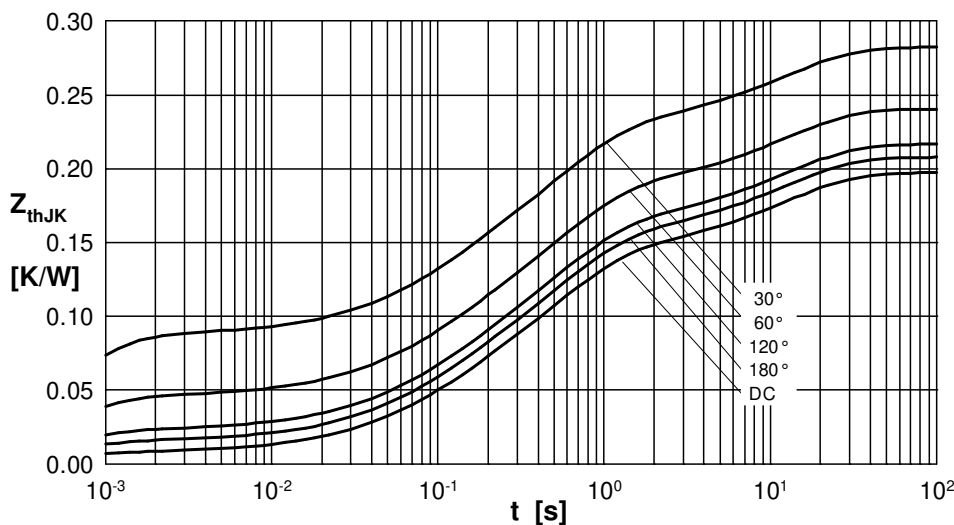


Fig. 11 Transient thermal impedance junction to heatsink (per thyristor/diode)

$R_{thJK}$  for various conduct. angles d:

d	$R_{thJK}$ (K/W)
DC	0.197
180°	0.208
120°	0.217
60°	0.240
30°	0.283

Constants for  $Z_{thJK}$  calculation:

i	$R_{th}$ (K/W)	t (s)
1	0.0076	0.00054
2	0.0406	0.09800
3	0.0944	0.54000
4	0.0147	12.0000
5	0.0400	12.0000